CREE

C3M0160120J

Silicon Carbide Power MOSFET
C3M™ MOSFET Technology

N-Channel Enhancement Mode

V_{DS}	1200 V
$I_{D\ @\ 25^{\circ}C}$	17 A
$R_{DS(on)}$	160 mΩ

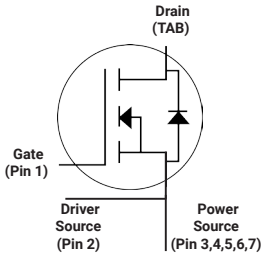
Features

- 3rd generation SiC MOSFET technology
- Low impedance package with driver source pin
- 7mm of creepage distance between drain and source
- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen free, RoHS compliant

Package

Halogen-Free

RoHS



Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Applications

- Renewable energy
- High voltage DC/DC converters
- Switch Mode Power Supplies
- UPS

Part Number	Package	Marking
C3M0160120J	TO-263-7	C3M0160120J

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	V_{GS} = 0 V, I_D = 100 µA	
V_{GSmax}	Gate - Source Voltage (dynamic)	-8/+19	V	AC (f >1 Hz)	Note: 1
V_{GSop}	Gate - Source Voltage (static)	-4/+15	V	Static	Note: 2
I_D	Continuous Drain Current	17	A	V_{GS} = 15 V, T_C = 25˚C	Fig. 19
		12		V_{GS} = 15 V, T_C = 100˚C	
$I_{D(pulse)}$	Pulsed Drain Current	34	A	Pulse width t_P limited by T_{jmax}	Fig. 22
P_D	Power Dissipation	90	W	T_C=25˚C, T_J = 150 ˚C	Fig. 20
T_J , T_{stg}	Operating Junction and Storage Temperature	-55 to +150	˚C		
T_L	Solder Temperature	260	˚C	1.6mm (0.063”) from case for 10s	

Note (1): When using MOSFET Body Diode V_{GSmax} = -4V/+19V
Note (2): MOSFET can also safely operate at 0/+15 V

Electrical Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	V_{GS} = 0 V, I_D = 100 µA	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.8	3.6	V	V_{DS} = V_{GS}, I_D = 2.33 mA	Fig. 11
			2.2		V	V_{DS} = V_{GS}, I_D = 2.33 mA, T_J = 150°C	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	µA	V_{DS} = 1200 V, V_{GS} = 0 V	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	V_{GS} = 15 V, V_{DS} = 0 V	
$R_{DS(on)}$	Drain-Source On-State Resistance		160	208	mΩ	V_{GS} = 15 V, I_D = 8.5 A	Fig. 4, 5, 6
			256			V_{GS} = 15 V, I_D = 8.5 A, T_J = 150°C	
g_{fs}	Transconductance		5.2		S	V_{DS}= 20 V, I_{DS}= 8.5 A	Fig. 7
			4.9			V_{DS}= 20 V, I_{DS}= 8.5 A, T_J = 150°C	
C_{iss}	Input Capacitance		632		pF	V_{GS} = 0 V, V_{DS} = 1000 V f = 1 MHz V_{AC} = 25 mV	Fig. 17, 18
C_{oss}	Output Capacitance		39				
C_{rss}	Reverse Transfer Capacitance		3				
E_{oss}	C_{oss} Stored Energy		22.5		µJ		Fig. 16
E_{ON}	Turn-On Switching Energy (Body Diode FWD)		64		µJ	V_{DS} = 800 V, V_{GS} = -4 V/15 V, I_D = 8.5 A, $R_{G(ext)}$ = 2.5 Ω, L= 336 µH	Fig. 26, 29
E_{OFF}	Turn-Off Switching Energy (Body Diode FWD)		13				
$t_{d(on)}$	Turn-On Delay Time		11		ns	V_{DD} = 800 V, V_{GS} = -4 V/15 V I_D = 8.5 A, $R_{G(ext)}$ = 0 Ω, Timing relative to V_{DS} Inductive load	Fig. 27, 28, 29
t_r	Rise Time		8				
$t_{d(off)}$	Turn-Off Delay Time		14				
t_f	Fall Time		8				
$R_{G(int)}$	Internal Gate Resistance		8		Ω	f = 1 MHz, V_{AC} = 25 mV	
Q_{gs}	Gate to Source Charge		11		nC	V_{DS} = 800 V, V_{GS} = -4 V/15 V I_D = 8.5 A Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		5				
Q_g	Total Gate Charge		24				

Reverse Diode Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	4.4		V	V_{GS} = -4 V, I_{SD} = 3 A	Fig. 8, 9, 10
		4.0		V	V_{GS} = -4 V, I_{SD} = 3 A, T_J = 150 °C	
I_S	Continuous Diode Forward Current		17	A	V_{GS} = -4 V	Note 1
$I_{S, pulse}$	Diode pulse Current		34	A	V_{GS} = -4 V, pulse width t_P limited by T_{jmax}	Note 1
t_{rr}	Reverse Recover time	5		ns	V_{GS} = -4 V, I_{SD} = 8.5 A, V_R = 800 V dif/dt = 8925 A/µs, T_J = 25 °C	Note 1, Fig. 29
Q_{rr}	Reverse Recovery Charge	65		nC		
I_{rrm}	Peak Reverse Recovery Current	19		A		
t_{rr}	Reverse Recover time	7		ns	V_{GS} = -4 V, I_{SD} = 8.5 A, V_R = 800 V dif/dt = 2020 A/µs, T_J = 25 °C	Note 1, Fig. 29
Q_{rr}	Reverse Recovery Charge	32		nC		
I_{rrm}	Peak Reverse Recovery Current	8		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.38	°C/W		Fig. 21

Typical Performance

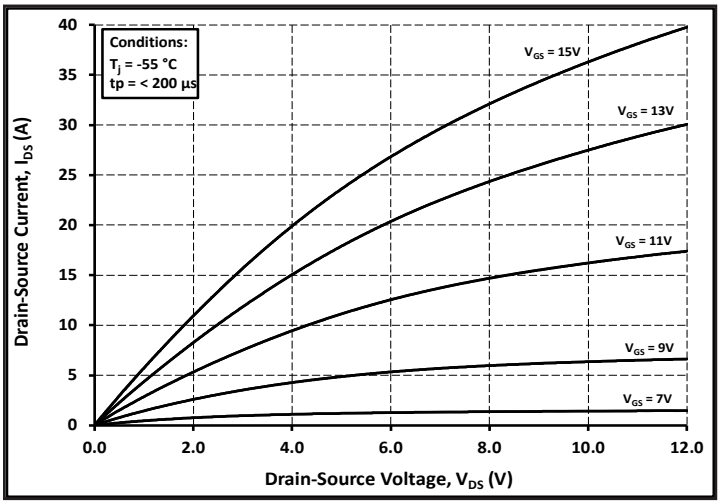


Figure 1. Output Characteristics T_J = -55 °C

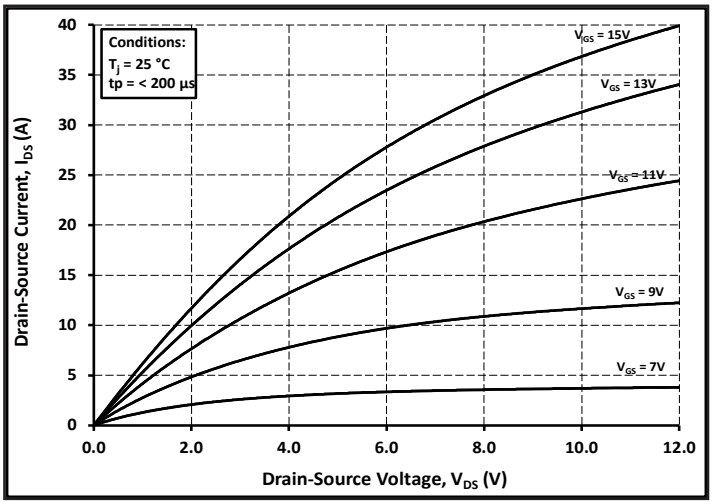


Figure 2. Output Characteristics T_J = 25 °C

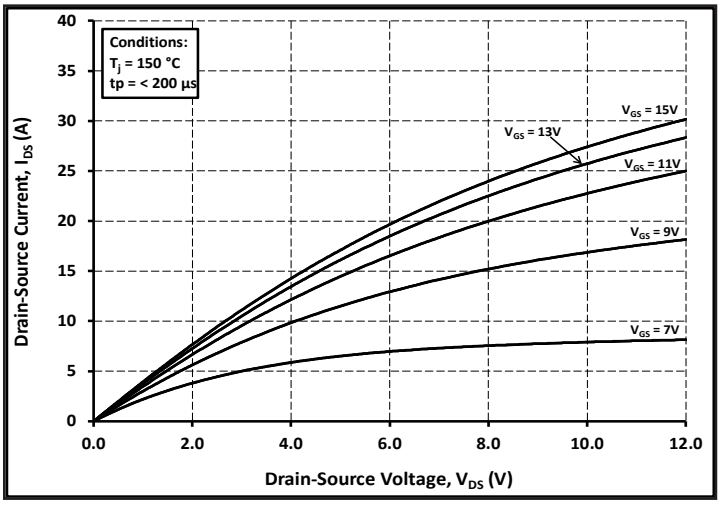


Figure 3. Output Characteristics T_J = 150 °C

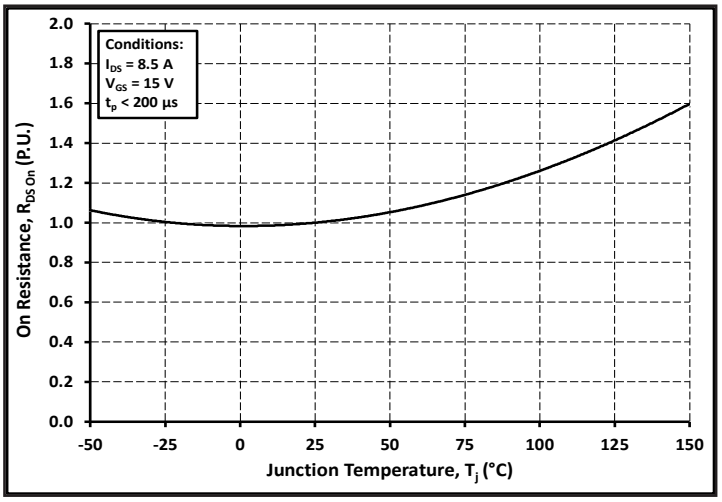


Figure 4. Normalized On-Resistance vs. Temperature

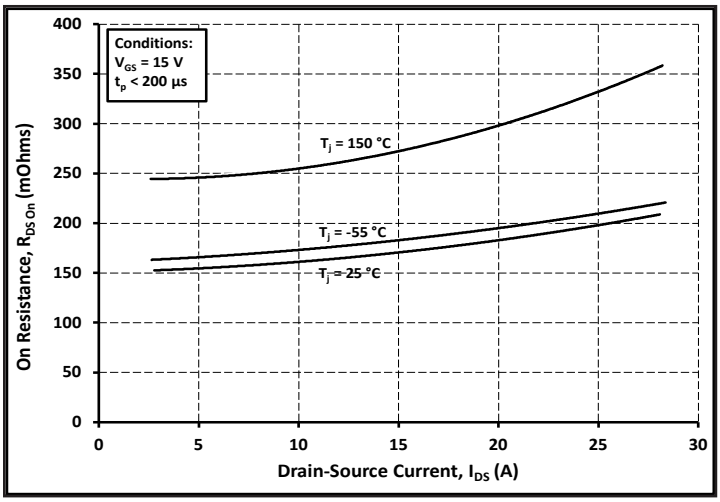


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

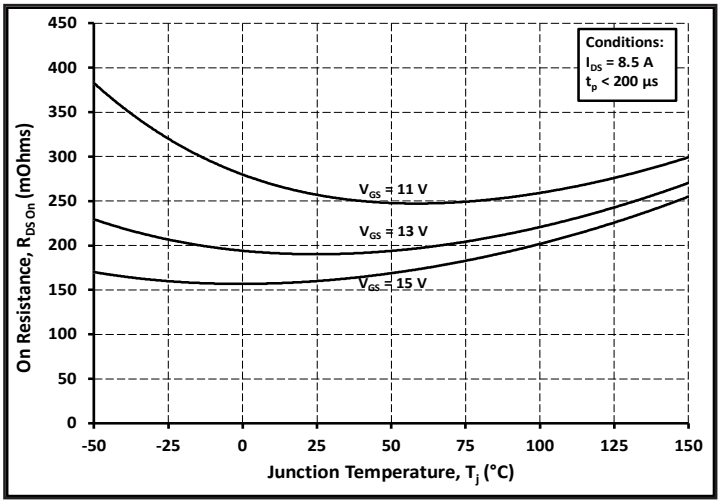


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

Typical Performance

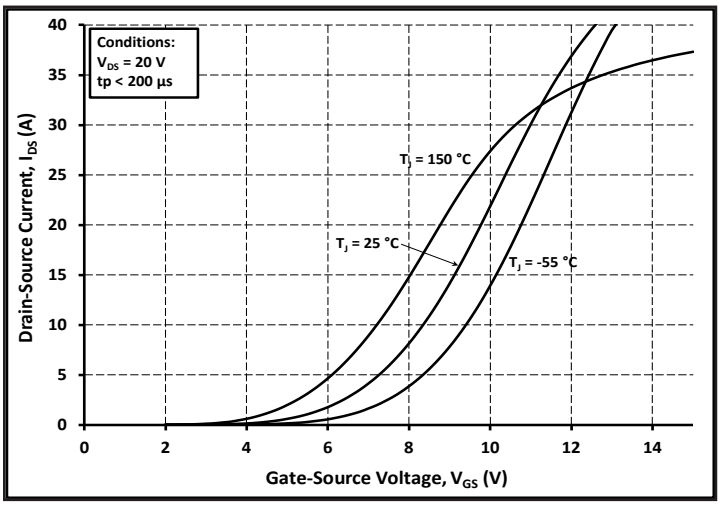


Figure 7. Transfer Characteristic for Various Junction Temperatures

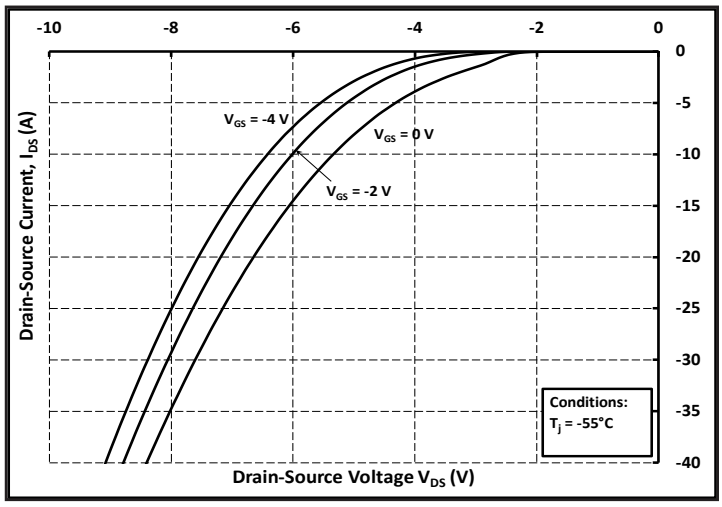


Figure 8. Body Diode Characteristic at -55 ºC

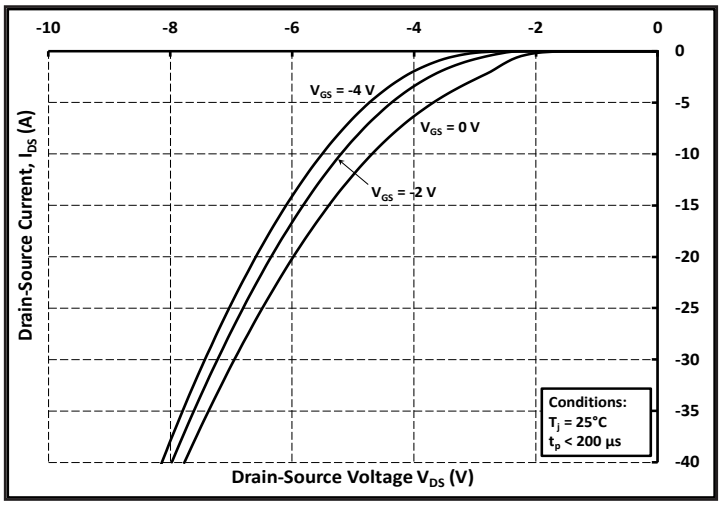


Figure 9. Body Diode Characteristic at 25 ºC

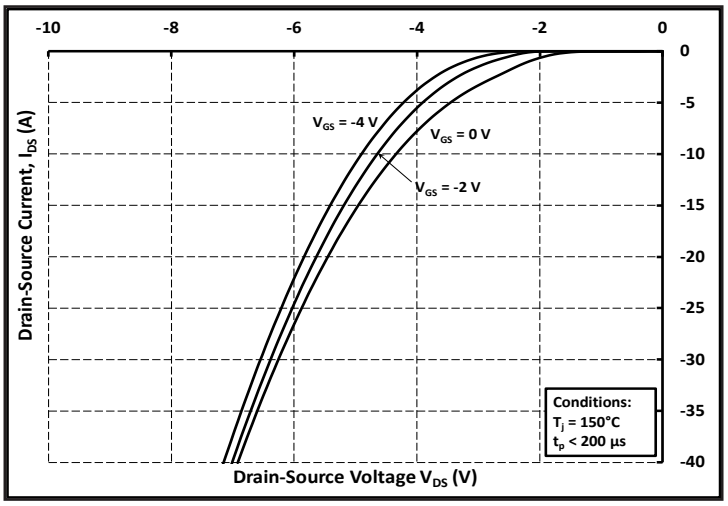


Figure 10. Body Diode Characteristic at 150 ºC

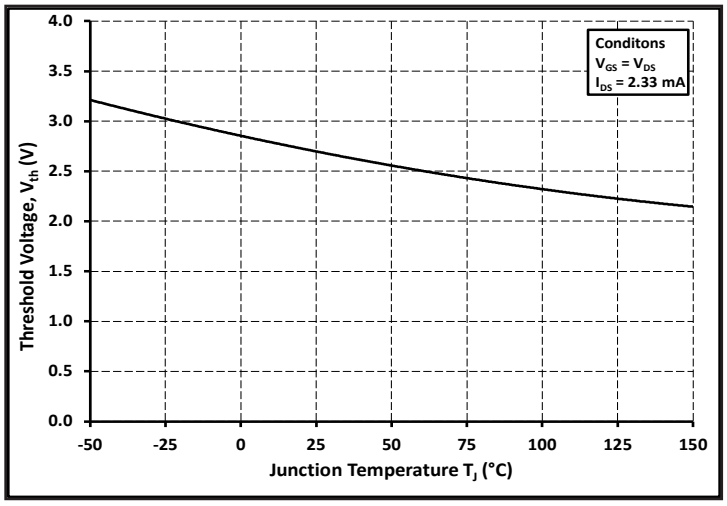


Figure 11. Threshold Voltage vs. Temperature

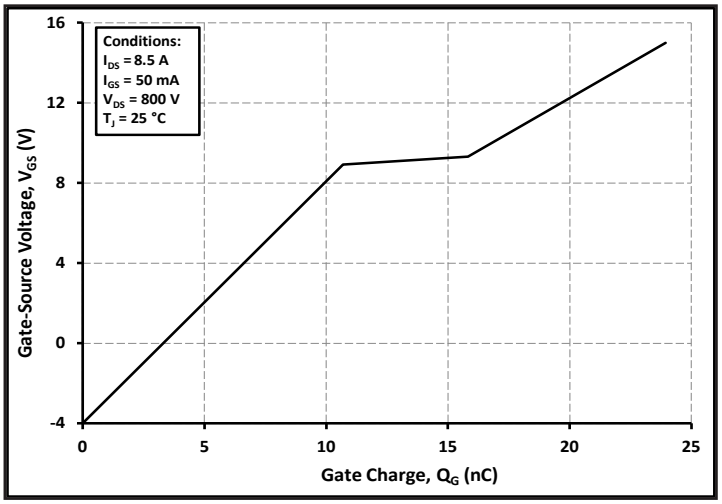


Figure 12. Gate Charge Characteristics

Typical Performance

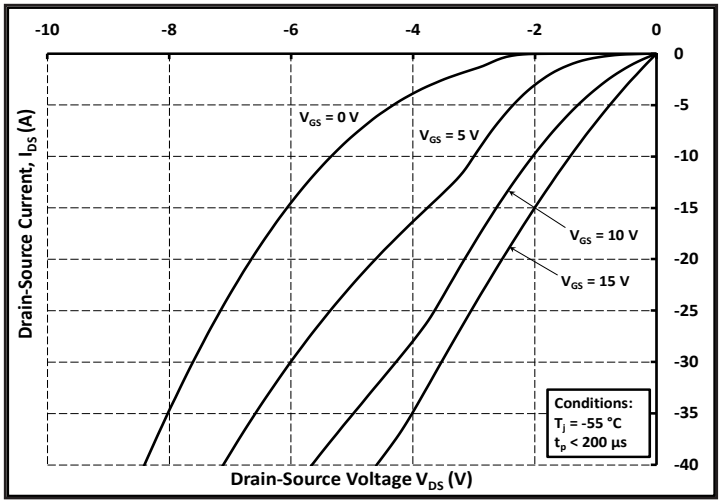


Figure 13. 3rd Quadrant Characteristic at -55 ºC

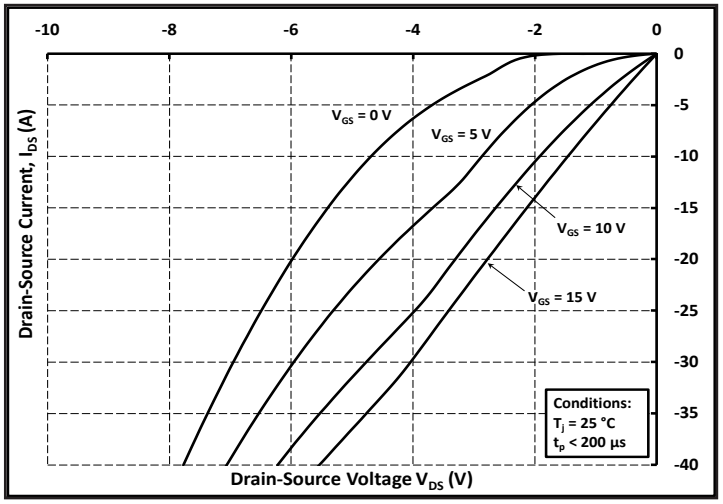


Figure 14. 3rd Quadrant Characteristic at 25 ºC

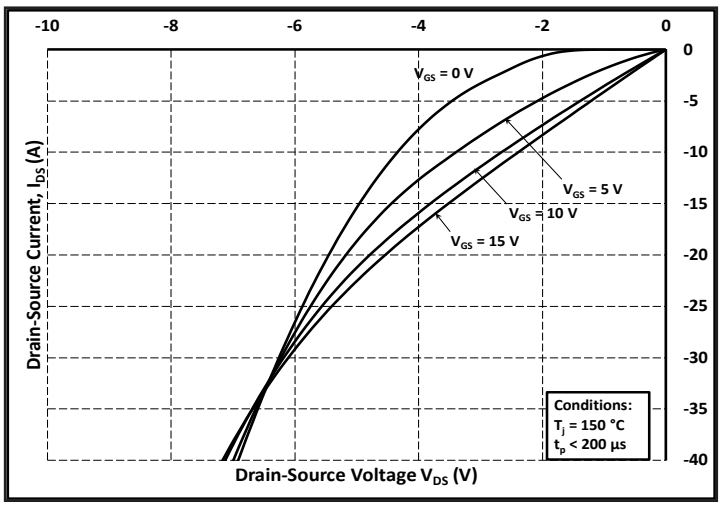


Figure 15. 3rd Quadrant Characteristic at 150 ºC

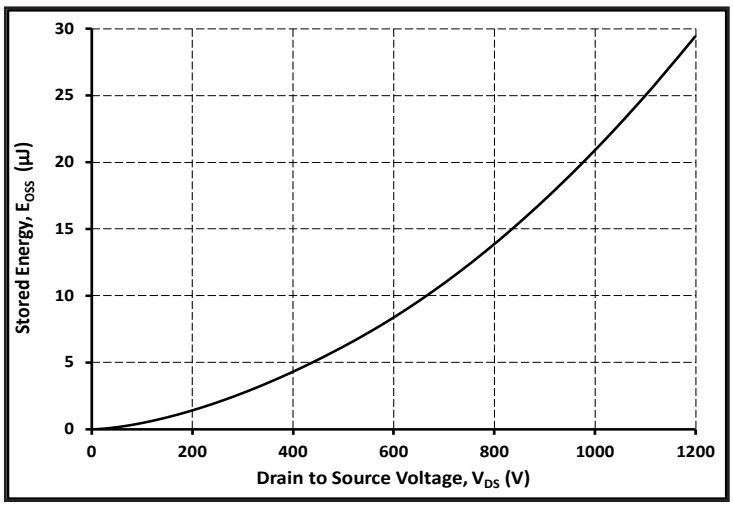


Figure 16. Output Capacitor Stored Energy

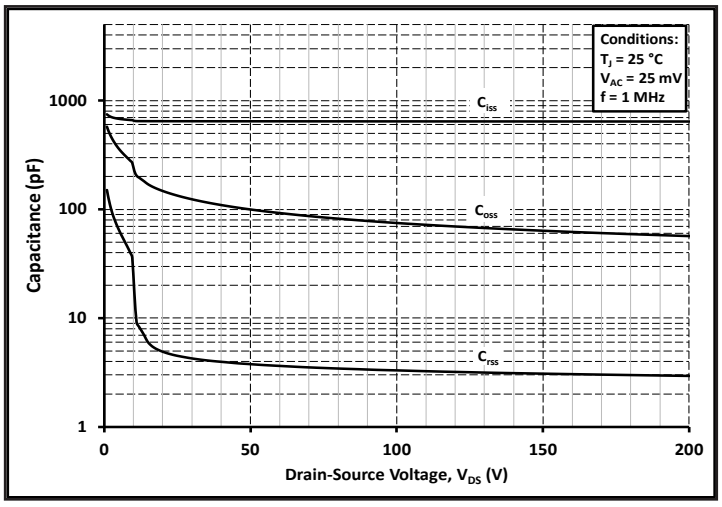


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

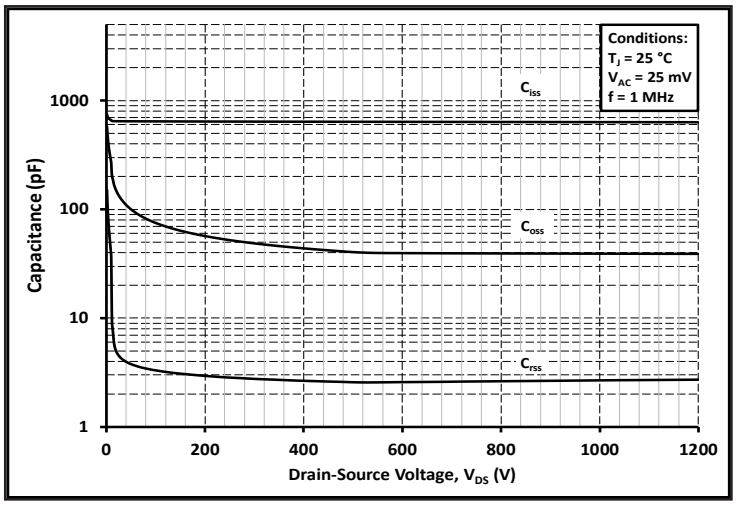


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1200V)

Typical Performance

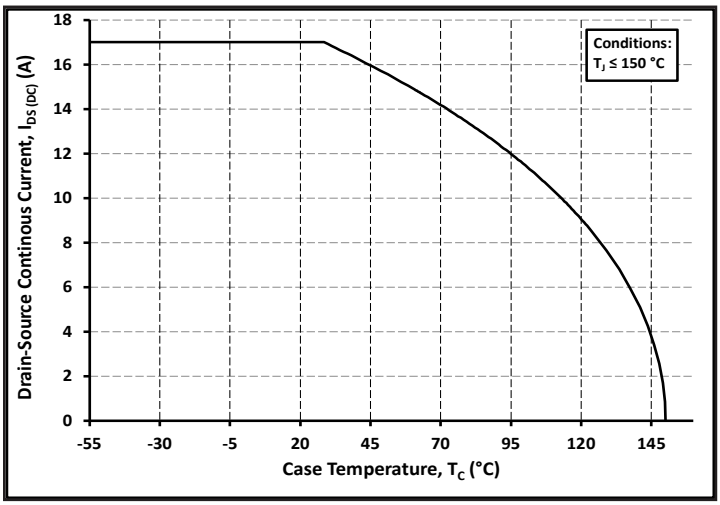


Figure 19. Continuous Drain Current Derating vs. Case Temperature

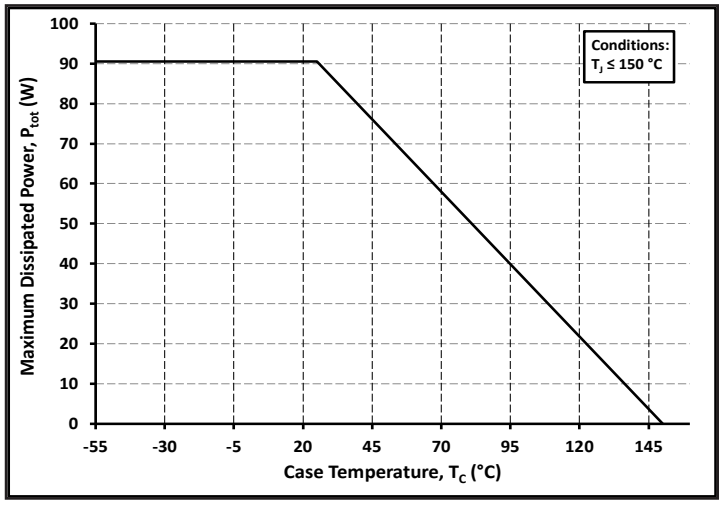


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

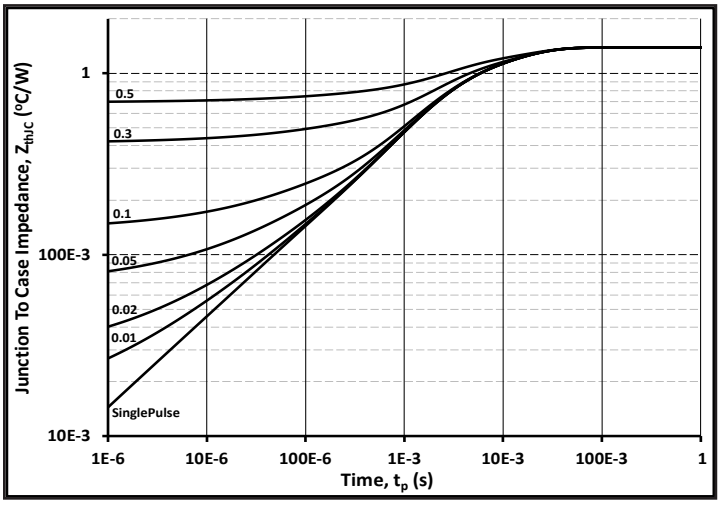


Figure 21. Transient Thermal Impedance (Junction - Case)

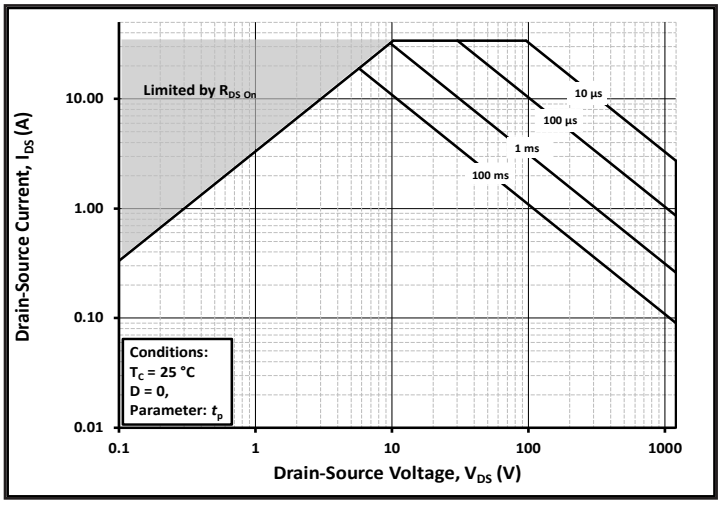


Figure 22. Safe Operating Area

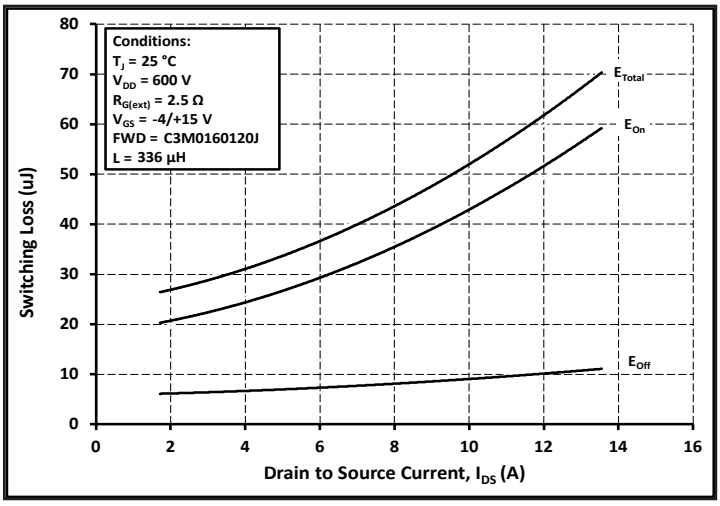


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 600V)

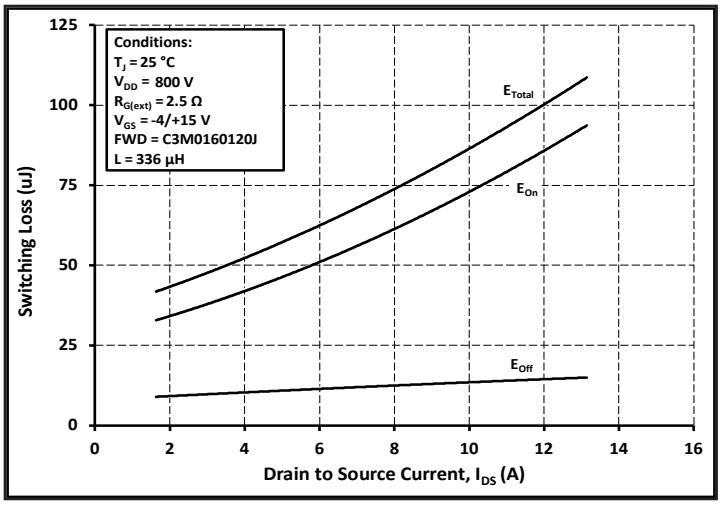


Figure 24. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 800V)

Typical Performance

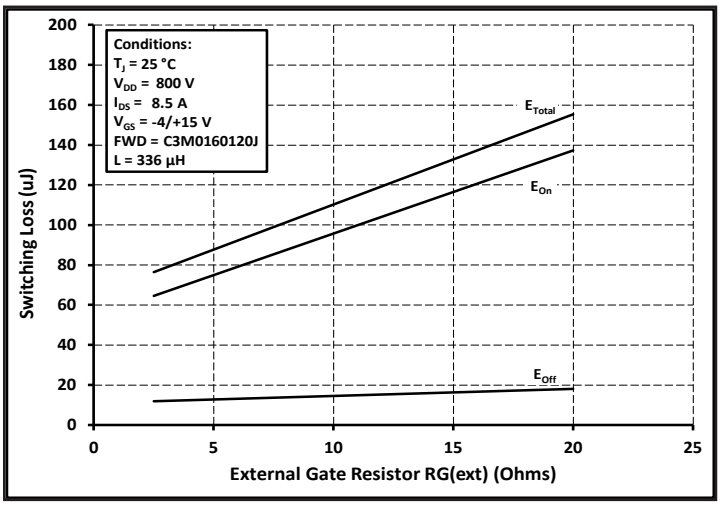


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

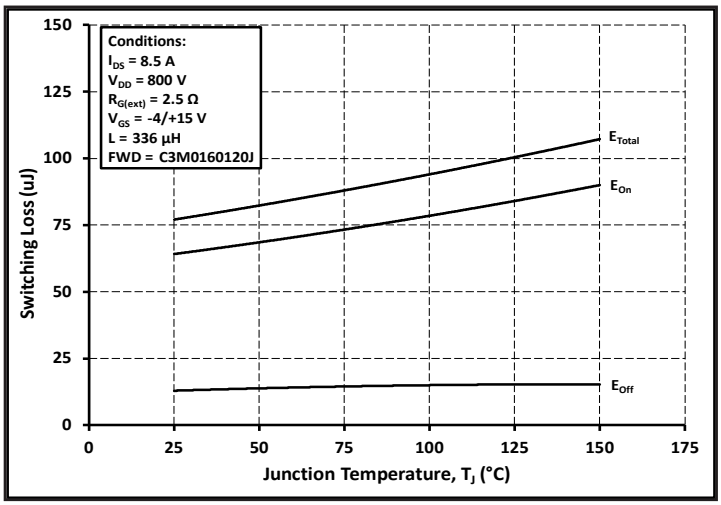


Figure 26. Clamped Inductive Switching Energy vs. Temperature

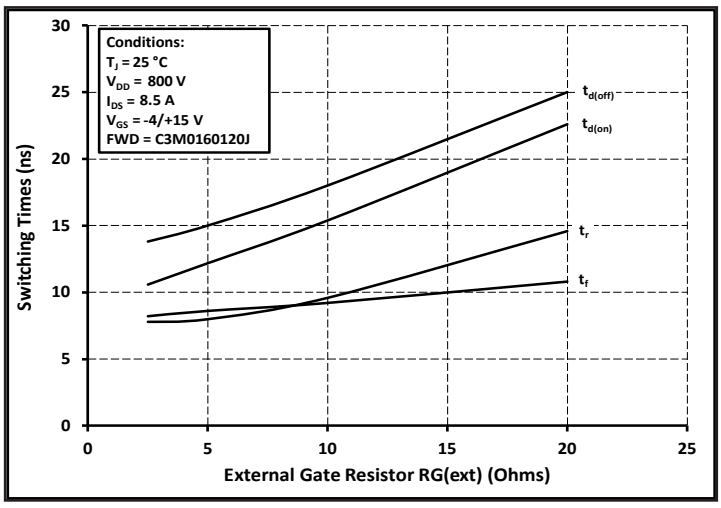


Figure 27. Switching Times vs. $R_{G(ext)}$

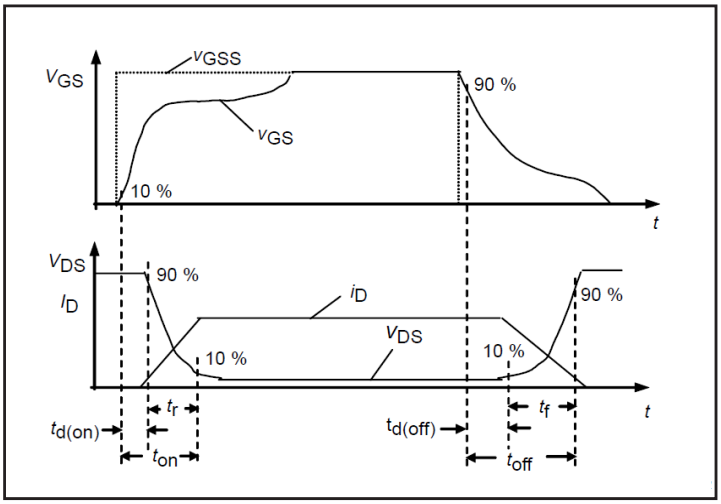


Figure 28. Switching Times Definition

Test Circuit Schematic

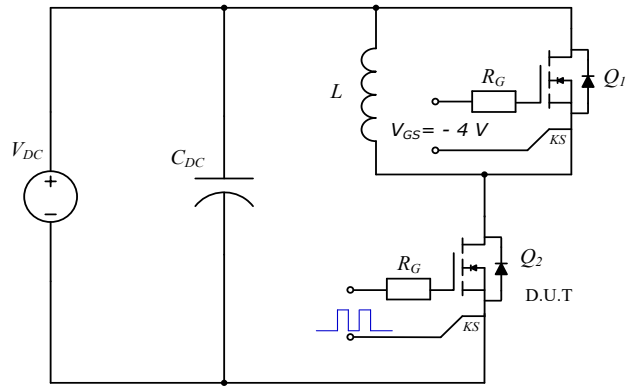
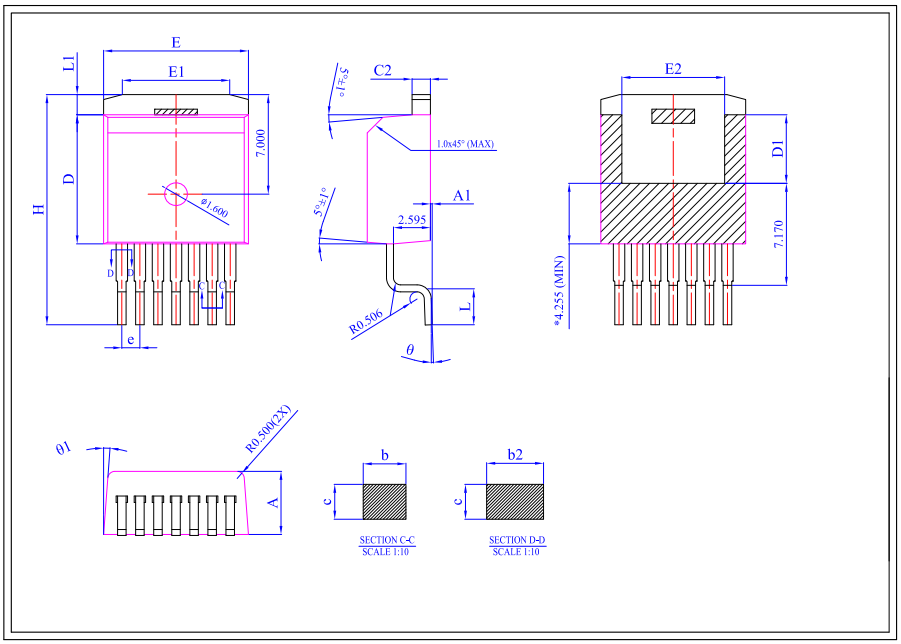


Figure 29. Clamped Inductive Switching Waveform Test Circuit

Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET Body Diode as shown above.

Package Dimensions

Package 7L D2PAK



Dim	All Dimensions in Millimeters		
	Min	typ	Max
A	4.300	4.435	4.570
A1	0.00	0.125	0.25
b	0.500	0.600	0.700
b2	0.600	0.800	1.000
c	0.330	0.490	0.650
C2	1.170	1.285	1.400
D	9.025	9.075	9.125
D1	4.700	4.800	4.900
E	10.130	10.180	10.230
E1	6.500	7.550	8.600
E2	6.778	7.223	7.665
e		1.27	
H	15.043	16.178	17.313
L	2.324	2.512	2.700
L1	0.968	1.418	1.868
Ø	0°	4°	8°
Ø1	4.5°	5°	5.5°